

HSB83YP

Silicon Epitaxial Planar Diode for High Voltage Switching

HITACHI

ADE-208-843(Z)

Rev 0

Mar 2000

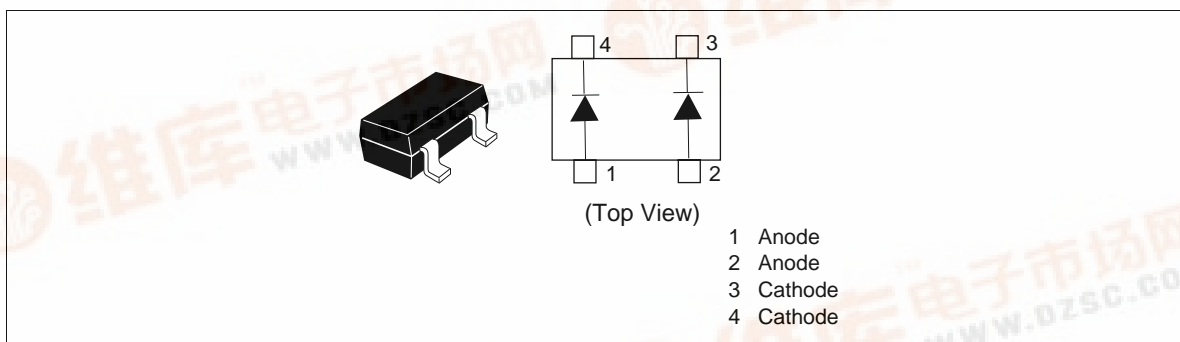
Features

- High reverse voltage. ($V_R=250V$)
- CMPAK- 4 package which has two devices parallel connection, is suitable for high density surface mounting.

Ordering Information

Type No.	Laser Mark	Package Code
HSB83YP	F7	CMPAK-4

Outline



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Absolute Maximum Ratings (Ta = 25°C) *²

Item	Symbol	Value	Unit
Peak reverse voltage	V _{RM}	300	V
Reverse voltage	V _R	250	V
Peak forward current	I _{FM}	300	mA
Non-Repetitive peak forward surge current	I _{FSM} * ¹	2	A
Average rectified current	I _O	100	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55Å +125	°C

Note 1. Value at duration of 10msec.

Note 2. Two device total.

Electrical Characteristics (Ta = 25°C) *¹

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V _F	—	—	1.2	V	I _F = 100 mA
Reverse current	I _{R1}	—	—	0.2	μA	V _R = 250V
	I _{R2}	—	—	100		V _R = 300V
Capacitance	C	—	—	3.0	pF	V _R = 0V, f = 1 MHz
Reverse recovery time	t _{rr}	—	—	100	ns	I _F = I _R =30 mA, I _{rr} = 3mA, R _L = 100Ω

Note 1. Per one device.

Main Characteristic

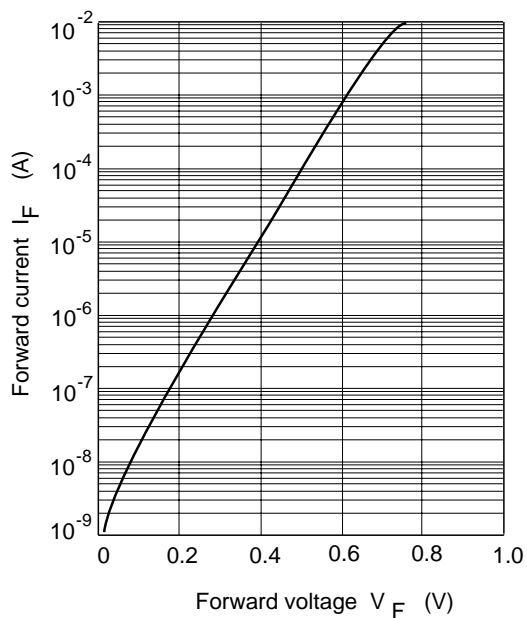


Fig.1 Forward current Vs. Forward voltage

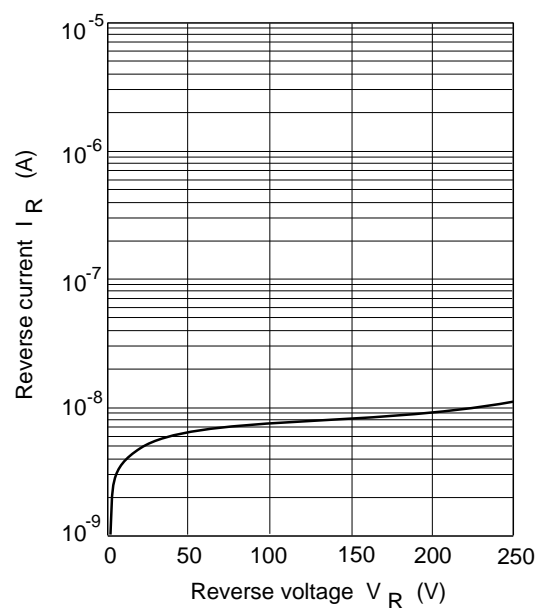


Fig.2 Reverse current Vs. Reverse voltage

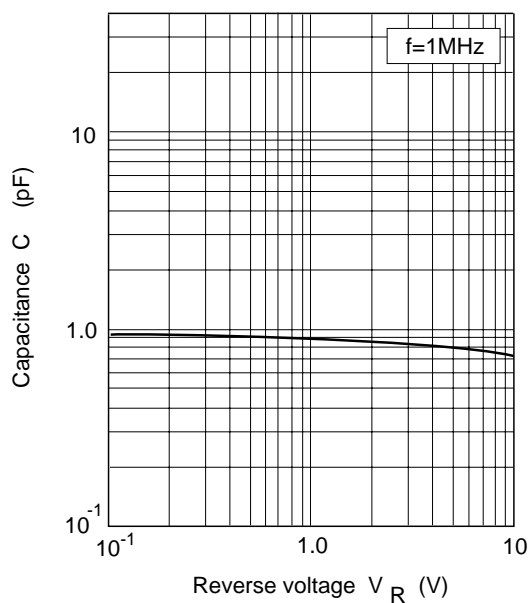
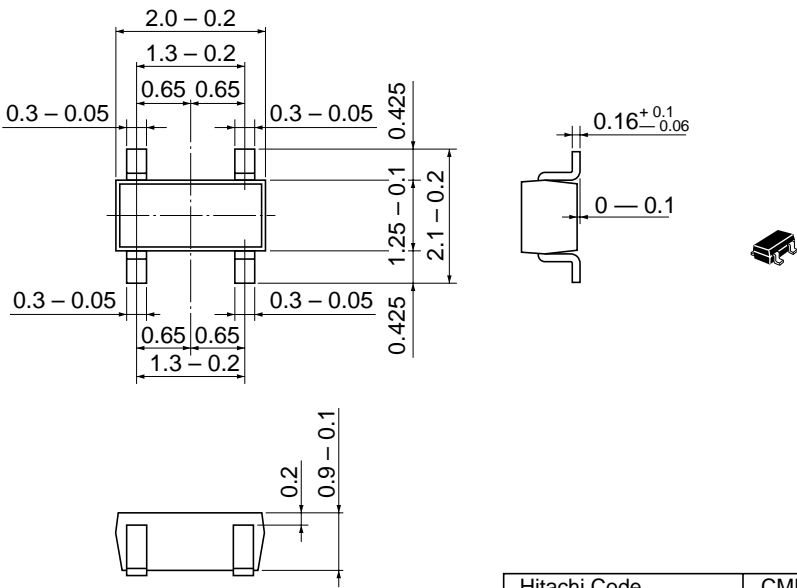


Fig.3 Capacitance Vs. Reverse voltage

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Package Dimensions

Unit: mm



Hitachi Code	CMPAK-4
JEDEC	
EIAJ	Conforms
Mass	0.006 g

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